

## General Description

The WSK200N08A is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSK200N08A meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

## Product Summary

$BV_{DSS}$	$R_{DSON}$	$I_D$
80V	3m $\Omega$	200A

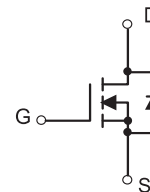
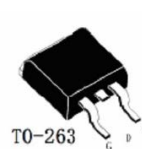
## Applications

High power DC/DC converters and switch mode

power supply

DC Motor control and Class D Amplifier

## TO-263 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	80	V
$V_{GS}$	Gate-Source Voltage	$\pm 25$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	200	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	144	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup> , $T_C=25^\circ C$	790	A
EAS	Avalanche Energy, Single pulse, $L=0.5mH$	1496	mJ
$I_{AS}$	Avalanche Current, Single pulse, $L=0.5mH$	200	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	345	W
$P_D@T_C=100^\circ C$	Total Power Dissipation <sup>4</sup>	173	W
$T_{STG}$	Storage Temperature Range	-55 to 175	$^\circ C$
$T_J$	Operating Junction Temperature Range	175	$^\circ C$

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	62.5	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	0.43	$^\circ C/W$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	80	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.096	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =100A	---	3.0	4.0	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	2.0	3.0	4.0	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5.5	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	10	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±25V, V <sub>DS</sub> =0V	---	---	±100	nA
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	3.2	---	Ω
Q <sub>g</sub>	Total Gate Charge (10V)	V <sub>DS</sub> =80V, V <sub>GS</sub> =10V, I <sub>D</sub> =30A	---	197	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	31	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	75	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =50V, V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω, I <sub>D</sub> =30A	---	28	---	ns
T <sub>r</sub>	Rise Time		---	18	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	42	---	
T <sub>f</sub>	Fall Time		---	54	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	8154	---	pF
C <sub>oss</sub>	Output Capacitance		---	1029	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	650	---	

**Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	V <sub>DD</sub> =25V, L=0.5mH, I <sub>AS</sub> =28A	160	---	---	mJ

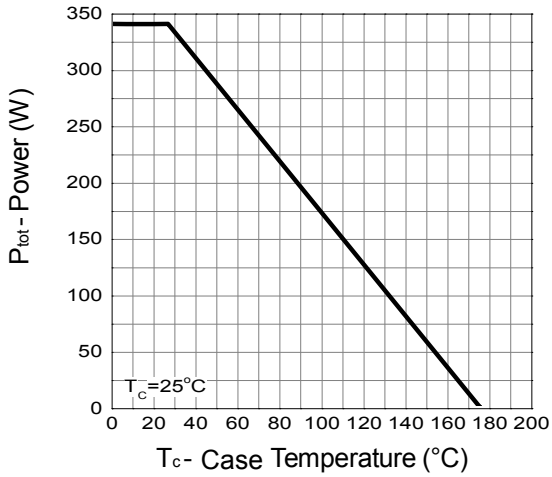
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	200	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>		---	---	350	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =15A, T <sub>J</sub> =25°C	---	---	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =15A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	30	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	52	---	nC

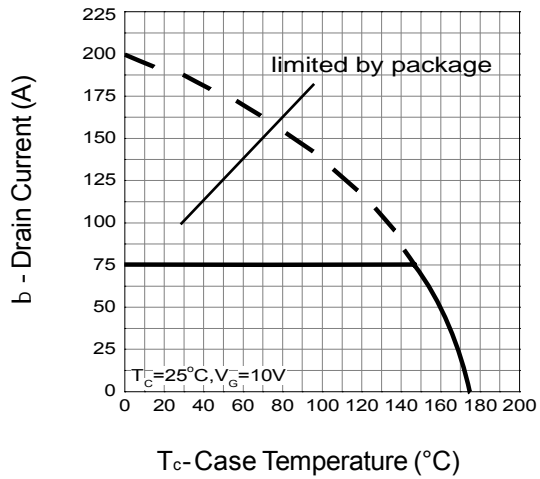
Note \* : Pulse test ; pulse width ≤300μs, duty cycle ≤2%.

**Typical Operating Characteristics**

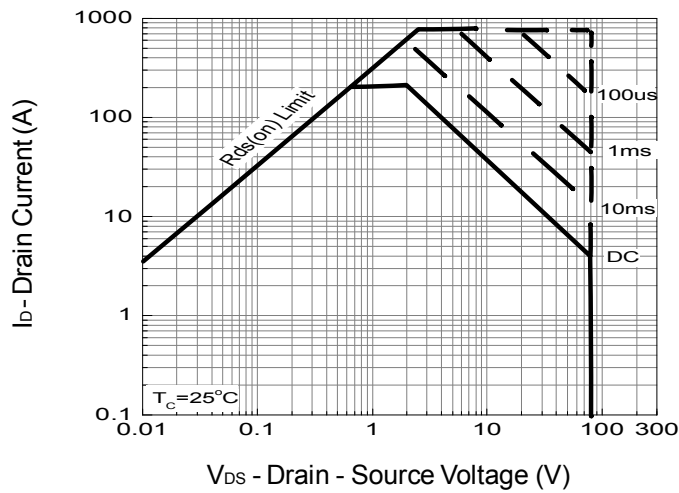
**Power Dissipation**



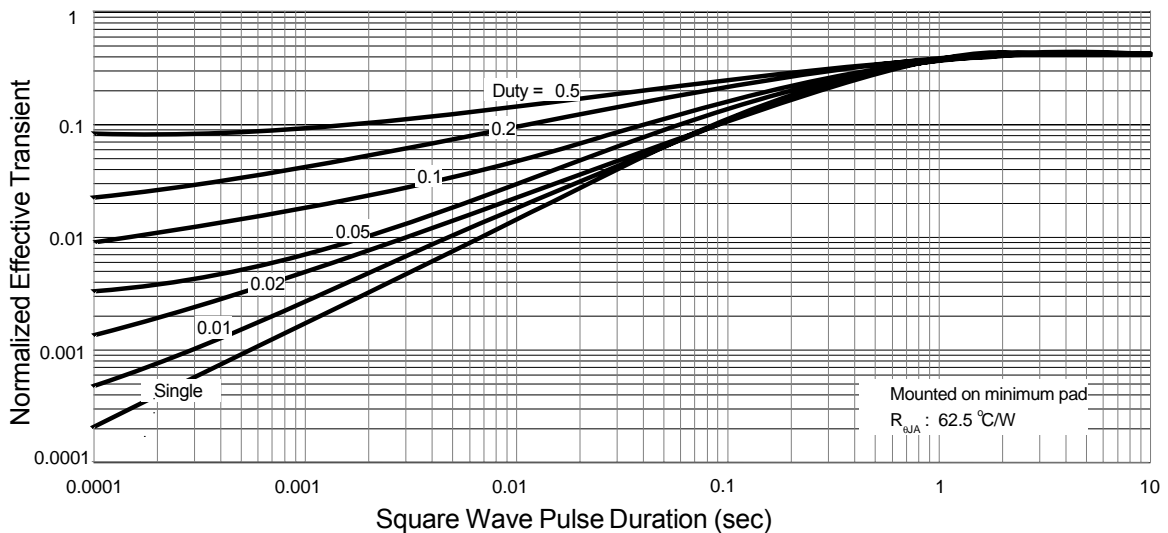
**Drain Current**



**Safe Operation Area**

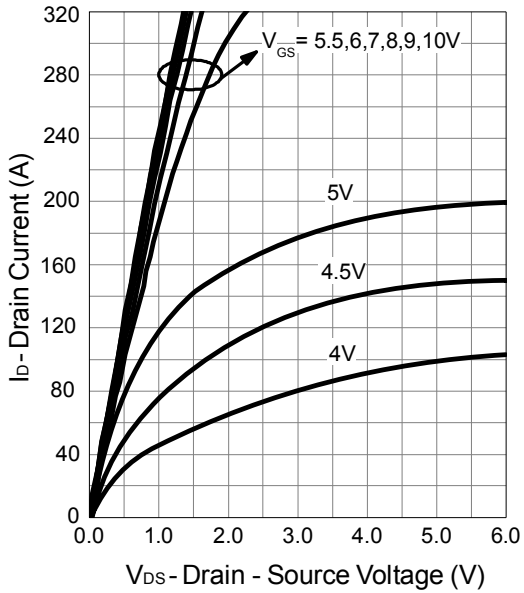


**Thermal Transient Impedance**

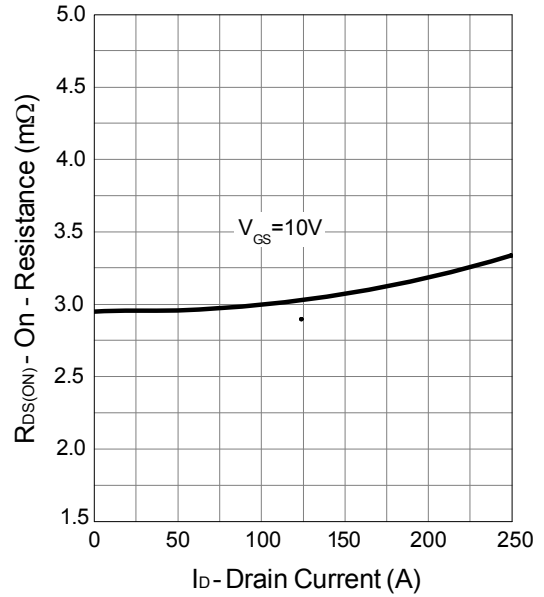


**Typical Operating Characteristics (Cont.)**

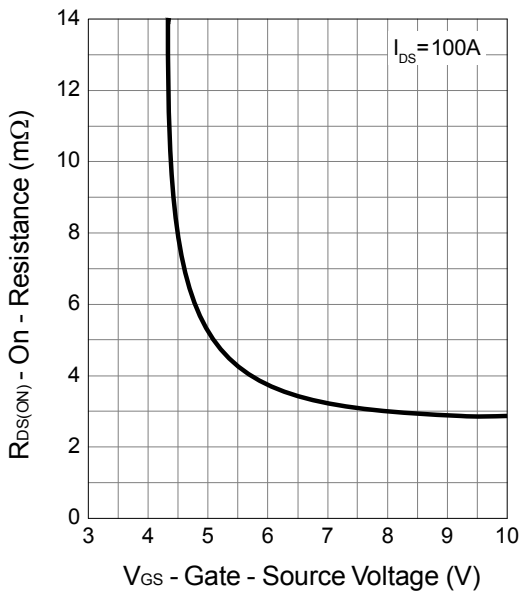
**Output Characteristics**



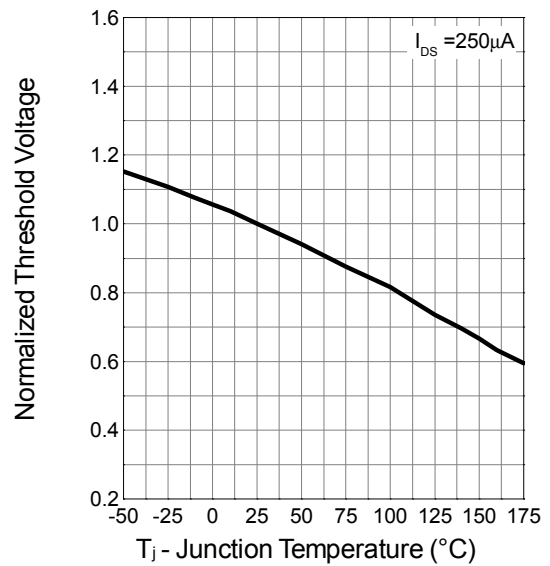
**Drain-Source On Resistance**



**Gate-Source On Resistance**

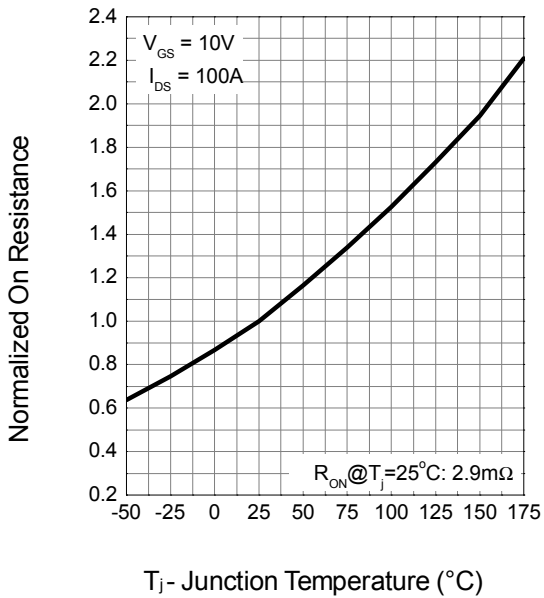


**Gate Threshold Voltage**

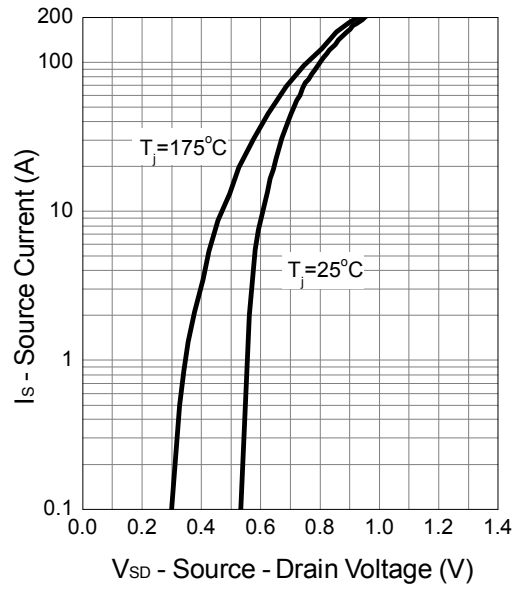


**Typical Operating Characteristics (Cont.)**

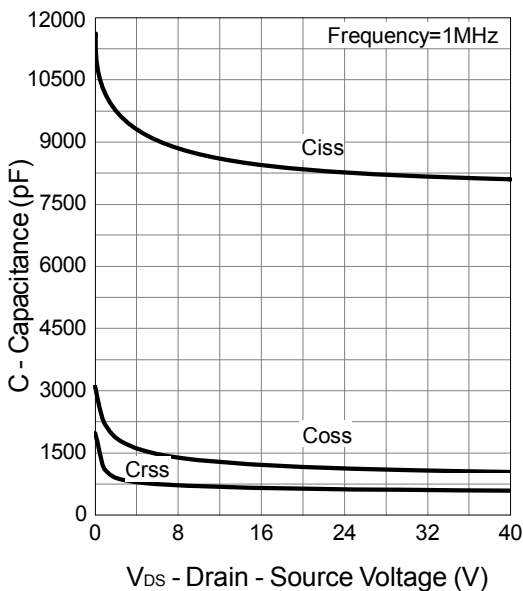
**Drain-Source On Resistance**



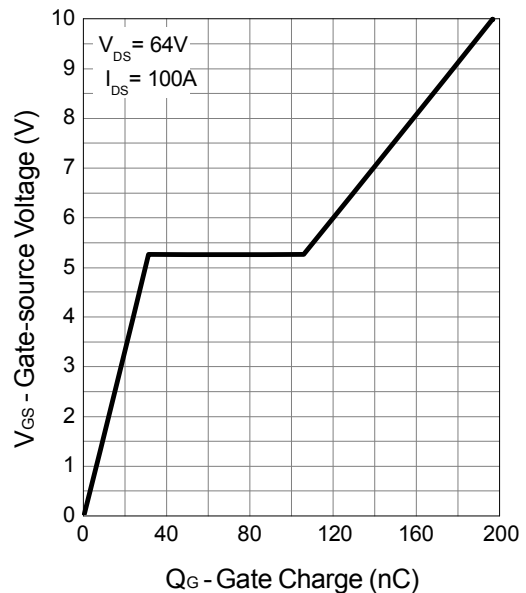
**Source-Drain Diode Forward**

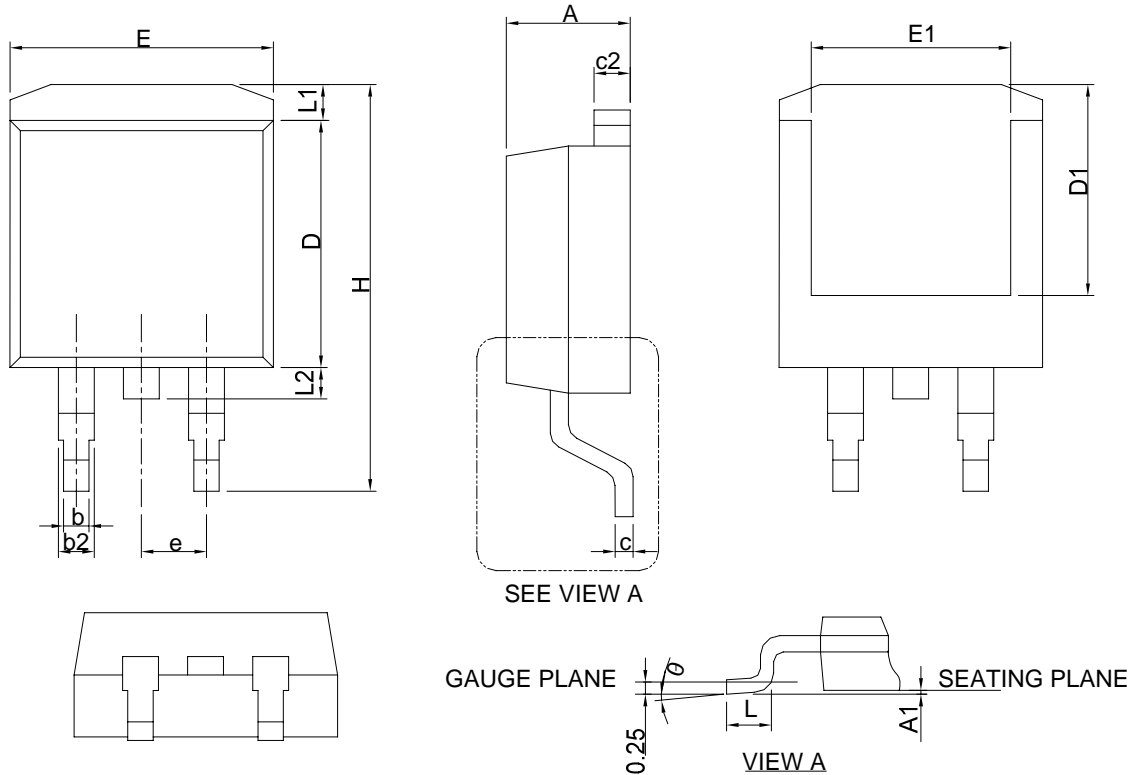


**Capacitance**

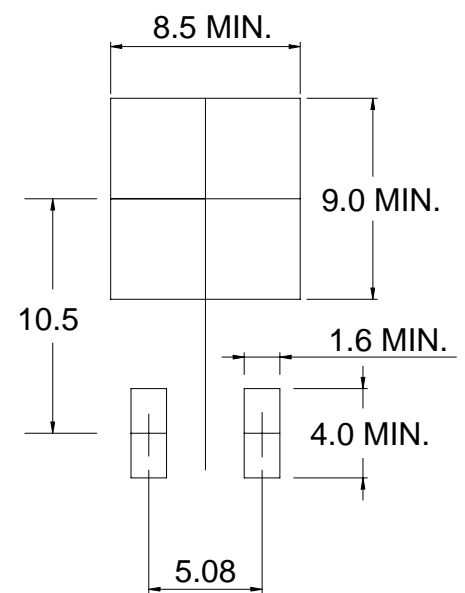


**Gate Charge**



**TO-263**


SYMBOL	TO-263			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b2	1.14	1.78	0.045	0.070
c	0.38	0.74	0.015	0.029
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380
D1	6.00	9.00	0.236	0.354
E	9.65	11.43	0.380	0.450
E1	6.22	9.00	0.245	0.354
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.68	-	0.066
L2	-	1.78	-	0.070
$\theta$	0°	8°	0°	8°

**RECOMMENDED LAND PATTERN**


UNIT: mm



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